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### REMARKS

Claims 18-19 and 22-27 are currently pending in the application. Claims 18, 19, 24 and 25 have been amended, and Claims 20 and 21 have been canceled. Claims 18 and 25 are independent claims.

A new title and Abstract is submitted herewith.

Consideration of this application in view of the foregoing amendments and the following remarks is respectfully requested.

#### New Title, Abstract and Claim Informalities

In accordance with the requirements set out in paragraphs 1-3 of the Office Action, a new title that is clearly indicative of the invention is proposed herein, and a new Abstract directed to the making of the semiconductor device is proposed.

In addition, each of the issues raised in paragraph 3 as to Claims 18, 19 and 24 has been addressed by the claim amendments presented above. Withdrawal of the objections is therefore respectfully requested.

#### Rejections Under 35 U.S.C. §102(b) and 35 U.S.C. §103(a)

Claims 18-20, 22, 23 and 26 were rejected under 35 USC 102(b) as being clearly anticipated by US Patent 5,442,214 (Yang); Claim 27 was rejected under 35 USC 103(a) as being unpatentable over Yang in view of US Patent 5,866,931 (Bulucca) and Claims 18 and 24 were rejected as being anticipated by US Patent 4,893,160 (Blanchard).

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Claims 21 and 25 were indicated to contain allowable subject matter.

Claims 20 and 21 have been canceled. The allowable limitations of Claim 21 have been incorporated into independent Claim 18, and Claim 25 has been rewritten in independent form to include all of the limitations of base Claim 18 and intervening Claim 24.

Generally, Yang shows a vertical double diffused metal-oxide-semiconductor (DMOS) transistor having a trench within an epitaxial layer. An implanted region is provided below the trench. Yang fails to teach or suggest a method of making a trench MOSFET device having a doped region formed within an epitaxial layer between a bottom portion of the trench and a substrate, where the doped region spans 100% of the distance from the trench bottom to the substrate.

Yang, and the other art of record, also fails to teach or suggest that the recited "elevated temperature" is provided in a step in which a sacrificial oxide is grown along walls of the trench.

Accordingly, applicants submit that independent Claims 18 and 25, as amended herein, are patentable over the cited references. Claims 19, 22-24 and 26-27 are dependent on, and contain all the limitations of, Claim 18, and as such are submitted to be patentable for at least the same reasons as Claim 18.

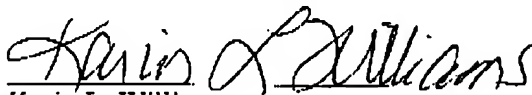
Applicants, therefore, submit that all claims are patentable over the cited references and that the application is in condition for allowance. If a telephone conference would facilitate examination of this application in any way, the examiner is invited to contact applicants' attorney at the telephone number below.

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No fee or extension of time is believed to be necessary for filing this amendment and response. If an extension of time is deemed to be necessary, however, such extension is hereby petitioned.

The Examiner's consideration of this matter is gratefully acknowledged.

Respectfully submitted,  
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**CERTIFICATE OF FACSIMILE TRANSMISSION**

I hereby certify that this document, and any document referenced herein, has been transmitted via facsimile to the US Patent and Trademark Office at (703) 872-9318 on August 18, 2004.

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